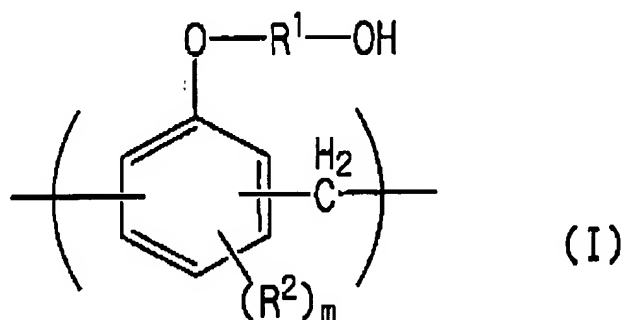


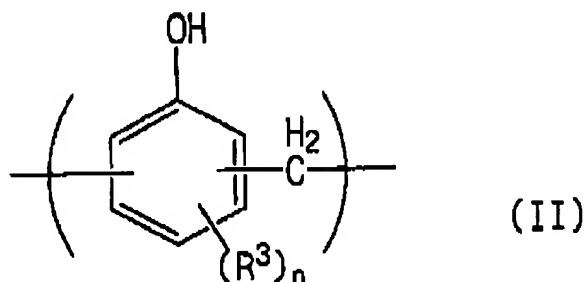
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### AMENDMENTS TO THE CLAIMS

1. (Original) A positive photoresist composition comprising an alkali-soluble novolak resin (A) containing a structural unit (a1) represented by a general formula (I) shown below:



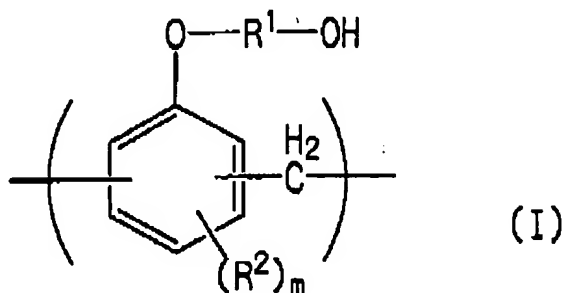
[wherein, R<sup>1</sup> represents an alkylene group of 1 to 5 carbon atoms, R<sup>2</sup> represents a hydrogen atom, a hydroxyl group, or an alkyl group of 1 to 4 carbon atoms, and m represents an integer of 1 to 3], and a structural unit (a2) represented by a general formula (II) shown below:



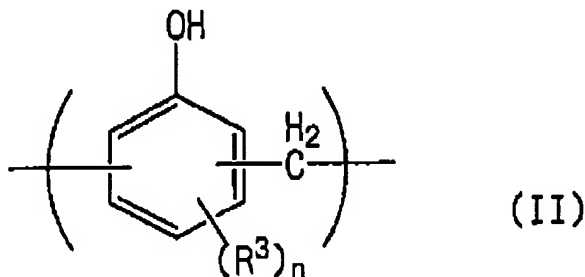
[wherein, R<sup>3</sup> represents a hydrogen atom, a hydroxyl group, or an alkyl group of 1 to 4 carbon atoms, and n represents an integer of 1 to 3], and a photosensitizer (B).

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2. (Original) A positive photoresist composition comprising an alkali-soluble novolak resin (A') containing a structural unit (a1) represented by a general formula (I) shown below:



[wherein, R<sup>1</sup> represents an alkylene group of 1 to 5 carbon atoms, R<sup>2</sup> represents a hydrogen atom, a hydroxyl group, or an alkyl group of 1 to 4 carbon atoms, and m represents an integer of 1 to 3], and a structural unit (a2) represented by a general formula (II) shown below:



[wherein, R<sup>3</sup> represents a hydrogen atom, a hydroxyl group, or an alkyl group of 1 to 4 carbon atoms, and n represents an integer of 1 to 3], wherein a portion of hydrogen atoms of said hydroxyl groups contained within said resin are substituted with 1,2-naphthoquinonediazidesulfonyl groups.

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3. **(Original)** A positive photoresist composition according to claim 2, further comprising a photosensitizer (B).

4. **(Currently Amended)** A method of forming a resist pattern comprising the steps of applying a positive photoresist composition according to any one of claim 1 through claim 3 to a substrate, conducting a prebake, performing selective exposure, and then performing alkali developing to form the resist pattern.